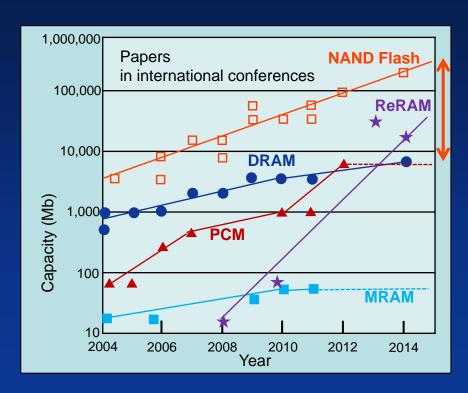


ReRAM Technology Perspective

Amigo Tsutsui
Sony Corporation



SCM is between NAND and DRAM

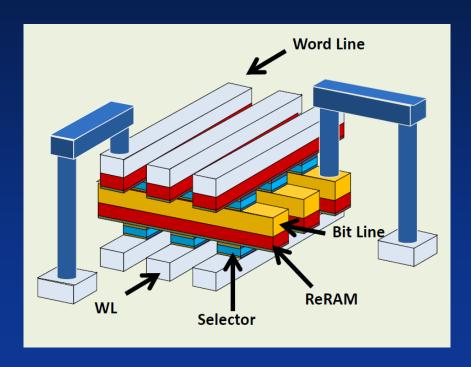


Emerging Memory Technologies

- MRAM is far from the target
- PCM looks like less improvement
- ReRAM is newcomer to grow up
- ReRAM is powerful candidate
- Need more capacity for the future



Cross Point for Higher Capacity



The key: Selector and Integration

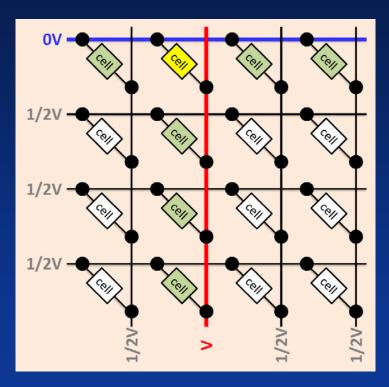
- CP R&D has long history
- But still under R&D



What are essential challenges?



Big Array of Cross Point Chip



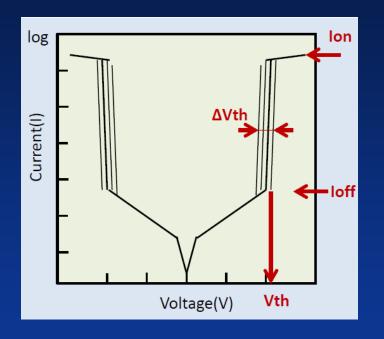
- Big array is used to realize higher capacity
- Half selected cells are over 1k for example
- Need to treat long word line and bit line
- Need scaling to realize higher capacity



High current makes the chip design difficult (ReRAM: ~50uA, PCM: >100uA)



Challenges of Selector Technology



Challenge	Issues	
High Vth	Retention	Δ
Small \Delta Vth	Endurance, Temp, Drift	×
Low loff	Leak, Array Size	Δ
Ion (~50uA)	Reliability	0

Most challenge for the product is "Small ΔVth"



In case of PCM, Ion > 100uA is more challenge



- CP is key to realize higher capacity chip
- Advantages of ReRAM over PCM in CP design
- We have still challenges of CP technology